

DS32EV100 Programmable Single Equalizer

Check for Samples: DS32EV100

FEATURES

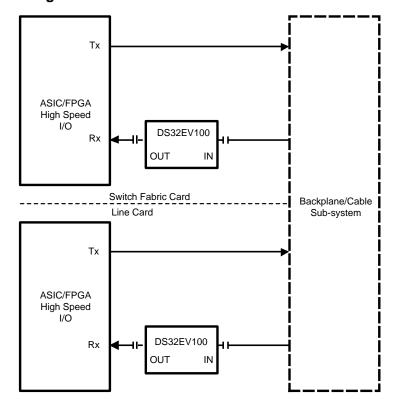
- Equalizes Up to 14 dB loss at 3.2 Gbps
- 8 levels of Programmable Equalization
- Operates up to 3.2 Gbps with 40" FR4 Traces
- 0.12 UI Residual Deterministic Jitter at 3.2 Gbps with 40" FR4 Traces
- Single 2.5V or 3.3V Power Supply
- Supports AC or DC-Coupling with Wide Input Common-Mode
- Low power Consumption: 100 mW Typ at 2.5V
- Small 3 mm x 4 mm 14-pin WSON Package
- > 8 kV HBM ESD Rating
- -40 to 85°C Operating Temperature Range

DESCRIPTION

The DS32EV100 programmable equalizer provides compensation for transmission medium losses and reduces the medium-induced deterministic jitter for NRZ data channel. The DS32EV100 is optimized for operation up to 3.2 Gbps for both cables and FR4 traces. The equalizer channel has eight levels of input equalization that can be programmed by three control pins.

The equalizer supports both AC and DC-coupled data paths for long run length data patterns such as PRBS-31, and balanced codes such as 8b/10b. The device uses differential current-mode logic (CML) inputs and outputs. The DS32EV100 is available in a 3 mm x 4 mm 14-pin WSON package. Power is supplied from either a 2.5V or 3.3V supply.

Simplified Application Diagram



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Pin Diagram

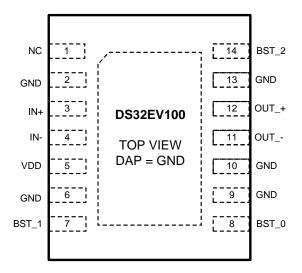


Figure 1. 14-Pin WSON Package (3 mm x 4 mm x 0.8 mm, 0.5 mm pitch) See Package Number NHK0014A

PIN DESCRIPTIONS(1)

			THE DECORM TIONS
Pin Name	Pin #	I/O, Type	Description
HIGH SPEED	DIFFERENTIA	L I/O	
IN- IN+	4 3	I, CML	Inverting and non-inverting CML differential inputs to the equalizer. An on-chip 100Ω terminating resistor is connected between IN+ and IN Refer to Figure 5.
OUT- OUT+	11 12	O, CML	Inverting and non-inverting CML differential outputs from the equalizer. An on-chip 50Ω terminating resistor connects OUT+ to V_{DD} and OUT- to V_{DD} .
EQUALIZATION	ON CONTROL		
BST_2 BST_1 BST_0	14 7 8	I, LVCMOS	BST_2, BST_1, and BST_0 select the equalizer strength. BST_2 is internally pulled high. BST_1 and BST_0 are internally pulled low.
POWER			
V _{DD}	5	Power	V_{DD} = 2.5V ±5% or 3.3V ±10%. V_{DD} pins should be tied to V_{DD} plane through low inductance path. A 0.01µF bypass capacitor should be connected between each V_{DD} pin to GND planes.
GND	2, 6, 9, 10, 13	Power	Ground reference. GND should be tied to a solid ground plane through a low impedance path.
DAP	PAD	Power	Ground reference. The exposed pad at the center of the package must be connected to ground plane of the board.
OTHER	•	•	
NC	1		Reserved. Leave no Connect.

(1) I = Input, O = Output



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

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Absolute Maximum Ratings (1)(2)

Supply Voltage (V _{DD})	-0.5V to +4.0V
CMOS Input Voltage	-0.5V to +4.0V
CMOS Output Voltage	-0.5V to +4.0V
CML Input/Output Voltage	-0.5V to +4.0V
Junction Temperature	+150°C
Storage Temperature	−65°C to +150°C
Lead Temperature Soldering, 4 sec	+260°C
ESD Rating	
HBM, 1.5 kΩ, 100 pF	> 8 kV
EIAJ, 0Ω, 200 pF	> 250 V
Thermal Resistance, $\theta_{JA}, \\ \text{No Airflow}$	40 °C/W

^{(1) &}quot;Absolute Maximum Ratings" indicate limits beyond which damage to the device may occur, including inoperability and degradation of device reliability and/or performance. Functional operation of the device and/or non-degradation at the Absolute Maximum Ratings or other conditions beyond those indicated in the Recommended Operating Conditions is not implied. The Recommended Operating Conditions indicate conditions at which the device is functional and the device should not be operated beyond such conditions. Absolute Maximum Numbers are guaranteed for a junction temperature range of -40°C to +125°C. Models are validated to Maximum Operating Voltages only.

Recommended Operating Conditions

	Min	Тур	Max	Units
Supply Voltage (1)				
V _{DD2.5} to GND	2.375	2.5	2.625	V
V _{DD3.3} to GND	3.0	3.3	3.6	V
Ambient Temperature	-40	25	+85	°C

⁽¹⁾ The $V_{DD2.5}$ is V_{DD} = 2.5V ± 5% and $V_{DD3.3}$ is V_{DD} = 3.3V ± 10%.

Electrical Characteristics

Over recommended operating supply and temperature ranges unless otherwise specified. (1)(2)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
POWER			-			1
Р	Power Supply	V _{DD2.5}		100	150	mW
	Consumption	V _{DD3.3}		140	200	mW
N	Supply Noise Tolerance ⁽³⁾	50 Hz – 100 Hz 100 Hz – 10 MHz 10 MHz – 1.6GHz		100 40 10		mV_{P-P} mV_{P-P} mV_{P-P}
LVTTL DC	SPECIFICATIONS		-			
V _{IH}	High Level Input	V _{DD2.5}	1.6		$V_{DD2.5}$	V
	Voltage	V _{DD3.3}	2.0		V _{DD3.3}	V
V_{IL}	Low Level Input Voltage		-0.3		0.8	V

⁽¹⁾ Typical values represent most likely parametric norms at V_{DD} = 3.3V or 2.5V, T_A = 25°C., and at the Recommended Operation Conditions at the time of product characterization and are not guaranteed.

(3) Allowed supply noise (mV_{P-P} sine wave) under typical conditions.

²⁾ If Military/Aerospace specified devices are required, please contact the TI Sales Office/Distributors for availability and specifications.

⁽²⁾ The Electrical Characteristics tables list guaranteed specifications under the listed Recommended Operating Conditions except as otherwise modified or specified by the Electrical Characteristics Conditions and/or Notes. Typical specifications are estimations only and are not guaranteed.



Electrical Characteristics (continued)

Over recommended operating supply and temperature ranges unless otherwise specified. (1)(2)

Symbol	Parameter	Conditions	Min	Typ (1)	Max	Units
V _{OH}	High Level Output	$I_{OH} = -3mA$, $V_{DD2.5}$	2.0			V
	Voltage	$I_{OH} = -3mA$, $V_{DD3.3}$	2.4			V
V_{OL}	Low Level Output Voltage	$I_{OL} = 3mA$			0.4	V
I _{IN}	Input Current	$V_{IN} = V_{DD}$		+1.8	+15	μΑ
		V _{IN} = GND	-15	0		μΑ
I _{IN-P}	Input Leakage Current	$V_{IN} = V_{DD}$, with internal pull-down resistors		+95		μΑ
	with Internal Pull- Down/Up Resistors	V _{IN} = GND, with internal pull-up resistors	-20			μΑ
CML REC	EIVER INPUTS (IN+, IN-)					
V _{TX}	Source Transmit Launch Signal Level (IN diff)	AC-Coupled or DC-Coupled Requirement, Differential measurement at point A. (Figure 2)	400		1600	mV _{P-P}
V_{INTRE}	Input Threshold Voltage	Differential measurement at point B. (Figure 2)		120		mV_{P-P}
V_{DDTX}	Supply Voltage of Transmitter to EQ	DC-Coupled Requirement	1.6		V _{DD}	V
V _{ICMDC}	Input Common-Mode Voltage	DC-Coupled Requirement Differential measurement at point A. (Figure 2), (4)	V _{DDTX} -0.8		V _{DDTX} -0.2	V
R_{LI}	Differential Input Return Loss	100 MHz – 1.6 GHz, with fixture's effect de- embedded		10		dB
R _{IN}	Input Resistance	Differential Across IN+ and IN (Figure 5)	85	100	115	Ω
CML OUT	PUTS (OUT+, OUT-)					
V _{OD}	Output Differential Voltage Level (OUT diff)	Differential measurement with OUT+ and OUT-terminated by 50Ω to GND, AC-Coupled (Figure 3)	550	620	725	mV_{P-P}
V _{OCM}	Output Common-Mode Voltage	Single-ended measurement DC-Coupled with 50Ω terminations $^{(4)}$	V _{DD} -0.2		V _{DD} -0.1	V
t _R , t _F	Transition Time	20% to 80% of differential output voltage, measured within 1" from output pins. (Figure 3)	20		60	ps
R _O	Output Resistance	Single-ended to V _{DD}	42	50	58	Ω
R _{LO}	Differential Output Return Loss	100 MHz – 1.6 GHz, with fixture's effect de- embedded. IN+ = static high.		10		dB
t _{PLHD}	Differential Low to High Propagation Delay	Propagation delay measurement at 50% V _{OD} between input to output, 100 Mbps (Figure 4), ⁽⁴⁾		240		ps
t _{PHLD}	Differential High to Low Propagation Delay			240		ps
EQUALIZA	ATION		*		- '	
DJ1	Residual Deterministic Jitter at 3.2 Gbps	40" of 6 mil microstrip FR4, EQ Setting 0x06, PRBS-7 (2 ⁷ -1) pattern		0.12	0.2	UI_P-P
DJ2	Residual Deterministic Jitter at 2.5 Gbps	40" of 6 mil microstrip FR4, EQ Setting 0x06, PRBS-7 (2 ⁷ -1) pattern (5) (6)		0.1	0.16	UI _{P-P}

⁽⁴⁾ Measured with clock-like {11111 00000} pattern.

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⁽⁵⁾ Specification is guaranteed by characterization at optimal boost setting and is not tested in production.

⁽⁶⁾ Deterministic jitter is measured at the differential outputs (point C of Figure 2), minus the deterministic jitter before the test channel (point A of Figure 2). Random jitter is removed through the use of averaging or similar means.



Electrical Characteristics (continued)

Over recommended operating supply and temperature ranges unless otherwise specified. (1)(2)

Symbol	Parameter	Conditions	Min	Typ (1)	Max	Units
DJ3	Residual Deterministic Jitter at 1 Gbps	40" of 6 mil microstrip FR4, EQ Setting 0x06, PRBS-7 (2 ⁷ -1) pattern		0.05		UI _{P-P}
RJ	Random Jitter	(4) (7)		0.5		ps _{rms}

(7) Random jitter contributed by the equalizer is defined as sqrt $(J_{OUT}^2 - J_{IN}^2)$. J_{OUT} is the random jitter at equalizer outputs in ps_{rms}, see point C of Figure 2; J_{IN} is the random jitter at the input of the equalizer in ps_{rms}, see Figure 2.

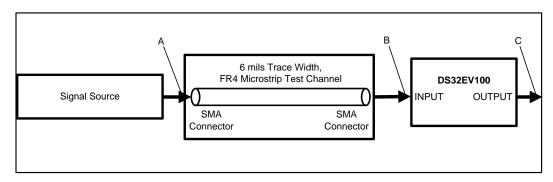


Figure 2. Test Setup Diagram

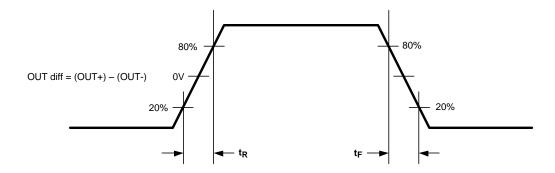


Figure 3. CML Output Transition Times

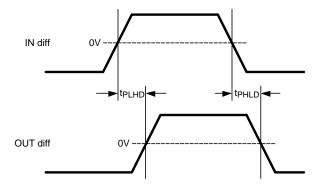


Figure 4. Propagation Delay Timing Diagram

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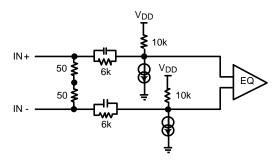


Figure 5. Simplified Receiver Input Termination Circuit

DS32EV100 FUNCTIONAL DESCRIPTIONS AND APPLICATIONS INFORMATION

The DS32EV100 is a programmable equalizer optimized for operation up to 3.2 Gbps for backplane and cable applications. The equalizer channel consists of an equalizer stage, a limiting amplifier, a DC offset correction block, and a CML driver as shown in Figure 6.

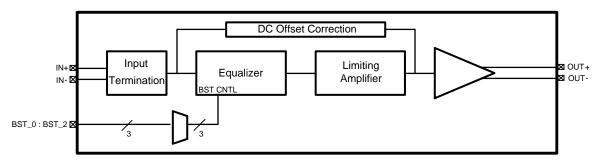


Figure 6. Simplified Block Diagram

EQUALIZER BOOST CONTROL

The equalizer channel supports eight programmable levels of equalization boost, and is controlled by the Boost Set pins (BST_[2:0]) in accordance with Table 1. The eight levels of boost settings enables the DS32EV100 to address a wide range of media loss and data rates.

Table 1. EQ Boost Control Table

6 mil Microstrip FR4 Trace Length (in)	24 AWG Twin-AX Cable Length (m)	Channel Loss 1.6 GHz (dB)	BST_N [2, 1, 0]
0	0	0	0 0 0
5	2	3	0 0 1
10	3	6	0 1 0
15	4	7	0 1 1
20	5	8	1 0 0 (Default)
25	6	10	1 0 1
30	7	12	1 1 0
40	10	14	1 1 1

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GENERAL RECOMMENDATIONS

The DS32EV100 is a high performance circuit capable of delivering excellent performance. Careful attention must be paid to the details associated with high-speed design as well as providing a clean power supply. Refer to the LVDS Owner's Manual for more detailed information on high-speed design tips to address signal integrity design issues.

PCB LAYOUT CONSIDERATIONS FOR DIFFERENTIAL PAIRS

The CML inputs and outputs must have a controlled differential impedance of 100Ω . It is preferable to route CML lines exclusively on one layer of the board, particularly for the input traces. The use of vias should be avoided if possible. If vias must be used, they should be used sparingly and must be placed symmetrically for each side of a given differential pair. Route the CML signals away from other signals and noise sources on the printed circuit board. See AN-1187 for additional information on WSON packages.

POWER SUPPLY BYPASSING

Two approaches are recommended to ensure that the DS32EV100 is provided with an adequate power supply. First, the supply (V_{DD}) and ground (GND) pins should be connected to power planes routed on adjacent layers of the printed circuit board. The layer thickness of the dielectric should be minimized so that the V_{DD} and GND planes create a low inductance supply with distributed capacitance. Second, careful attention to supply bypassing through the proper use of bypass capacitors is required. A $0.01\mu F$ bypass capacitor should be connected to each V_{DD} pin such that the capacitor is placed as close as possible to the DS32EV100. Smaller body size capacitors can help facilitate proper component placement. Additionally, three capacitors with capacitance in the range of $2.2~\mu F$ to $10~\mu F$ should be incorporated in the power supply bypassing design as well. These capacitors can be either tantalum or an ultra-low ESR ceramic and should be placed as close as possible to the DS32EV100.

DC COUPLING

The DS32EV100 supports both AC coupling with external ac coupling capacitor, and DC coupling to its upstream driver, or downstream receiver. With DC coupling, users must ensure the input signal common mode is within the range of the electrical specification V_{ICMDC} and the device output is terminated with 50 Ω to V_{DD} . When power-up and power-down the device, both the DS32EV100 and the downstream receiver should be power-up and power-down together. This is to avoid the internal ESD structures at the output of the DS32EV100 at power-down from being turned on by the downstream receiver.



Typical Performance Eye Diagrams and Curves

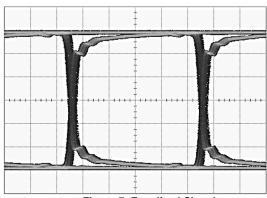


Figure 7. Equalized Signal (40 in FR4, 1 Gbps, PRBS 7, 0x07 Setting)

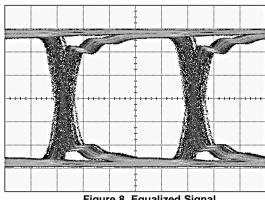


Figure 8. Equalized Signal (40 in FR4, 2.5 Gbps, PRBS 7, 0x07 Setting)

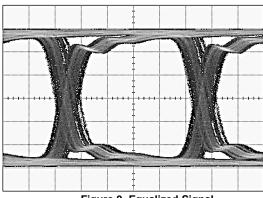


Figure 9. Equalized Signal (40 in FR4, 3.2Gbps, PRBS 7, 0x07 Setting)

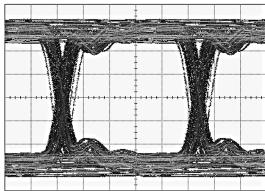


Figure 10. Equalized Signal (10m 24 AWG Twin-AX Cable, 3.2 Gbps, PRBS 7, 0x07 Setting)

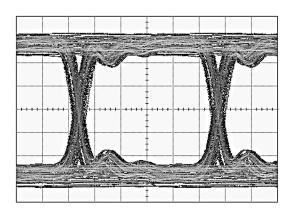


Figure 11. Equalized Signal (32 in Tyco XAUI Backplane, 3.125 Gbps, PRBS 7, 0x07 Setting

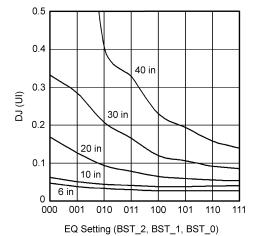


Figure 12. DJ vs. EQ Setting (3.2 Gbps)



REVISION HISTORY

CI	nanges from Revision C (February 2013) to Revision D	age
•	Changed layout of National Data Sheet to TI format	8



PACKAGE OPTION ADDENDUM

6-Feb-2020

PACKAGING INFORMATION

Orderable Device	Status	Package Type	U	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
DS32EV100SD/NOPB	ACTIVE	WSON	NHK	14	1000	Green (RoHS & no Sb/Br)	SN	Level-1-260C-UNLIM	-40 to 85	D32E1SD	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

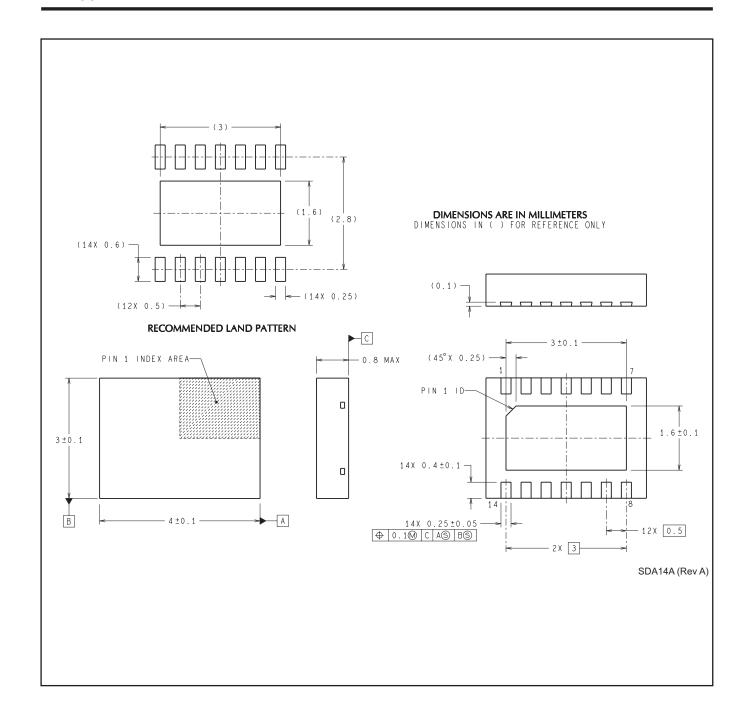
Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DS32EV100SD/NOPB	WSON	NHK	14	1000	178.0	12.4	3.3	4.3	1.0	8.0	12.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DS32EV100SD/NOPB	WSON	NHK	14	1000	210.0	185.0	35.0



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